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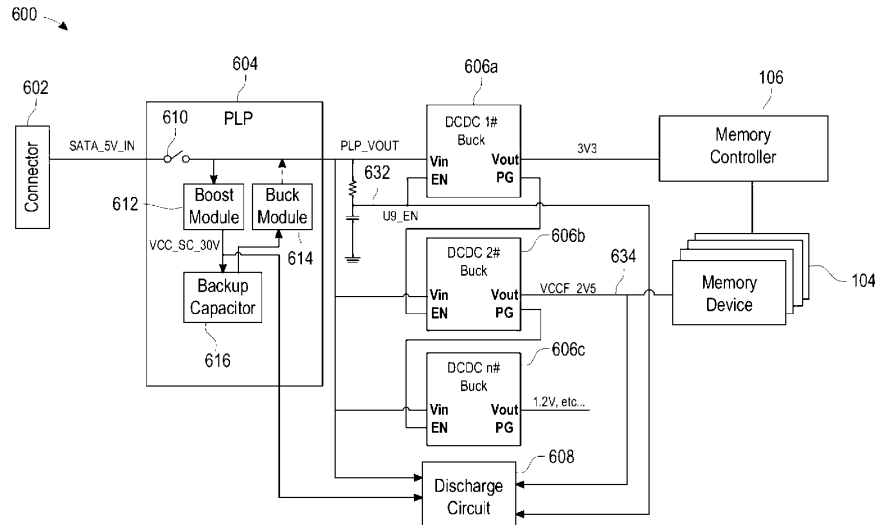


FIG. 6

(57) Abstract: Methods, devices, and systems for managing memory devices are provided. In one aspect, a memory system can include a memory device including memory cells, a memory controller coupled to the memory device, a power loss protection (PLP) circuit, and a discharge circuit coupled to an output of the PLP circuit. The discharge circuit includes one or more discharge paths configured to discharge at least one of the PLP circuit, the memory device, or the memory controller.

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